

## Vishay High Power Products

# **Medium Power**

# Silicon Rectifier Diodes, 12 A



#### DO-203AA (DO-4)

#### **FEATURES**

• Voltage ratings from 50 to 1000 V



• High surge capability

- · Low thermal impedance
- · High temperature rating
- · Can be supplied as JAN and JAN-TX devices in accordance with MIL-S-19500/260
- · RoHS compliant

PRODUCT SUMMARY			
I <sub>F(AV)</sub>	12 A		

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I <sub>F(AV)</sub>		12 <sup>(1)</sup>	Α		
	T <sub>C</sub>	150 <sup>(1)</sup>	°C		
I <sub>FSM</sub>	50 Hz	230	٨		
	60 Hz	240 (1)	А		
l <sup>2</sup> t	50 Hz	260	A <sup>2</sup> s		
	60 Hz	240	A-S		
T <sub>C</sub>		- 65 to 200	°C		
V <sub>RRM</sub>	Range	50 to 1000 <sup>(1)</sup>	V		

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS					
TYPE NUMBER (2)	V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V <sub>R(RMS)</sub> , MAXIMUM RMS REVERSE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	V <sub>RM</sub> , MAXIMUM DIRECT REVERSE VOLTAGE V	
	$T_C$ = - 65 °C TO 200 °C	$T_C$ = - 65 °C TO 200 °C	T <sub>C</sub> = - 65 °C TO 200 °C	$T_C$ = - 65 °C TO 200 °C	
1N1199A	50 <sup>(1)</sup>	35 <sup>(1)</sup>	100 (1)	50 <sup>(1)</sup>	
1N1200A	100 (1)	70 <sup>(1)</sup>	200 (1)	100 (1)	
1N1201A	150 <sup>(1)</sup>	105 <sup>(1)</sup>	300 (1)	150 <sup>(1)</sup>	
1N1202A	200 (1)	140 (1)	350 <sup>(1)</sup>	200 (1)	
1N1203A	300 (1)	210 <sup>(1)</sup>	450 <sup>(1)</sup>	300 <sup>(1)</sup>	
1N1204A	400 (1)	280 (1)	600 (1)	400 (1)	
1N1205A	500 <sup>(1)</sup>	350 <sup>(1)</sup>	700 <sup>(1)</sup>	500 <sup>(1)</sup>	
1N1206A	600 (1)	420 (1)	800 (1)	600 <sup>(1)</sup>	
1N3670A	700 (1)	490	900 (1)	700 <sup>(1)</sup>	
1N3671A	800 (1)	560	1000 (1)	800 (1)	
1N3672A	900 (1)	630	1100 (1)	900 (1)	
1N3673A	1000 (1)	700	1200 (1)	1000 (1)	

#### Notes

<sup>(1)</sup> JEDEC registered values

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<sup>(2)</sup> Basic part number indicates cathode to case; for anode to case, add "R" to part number, e.g., 1N1199RA

## 1N1...A, 1N36..A Series

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FORWARD CONDUCTION						
PARAMETER		SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average forward current		I <sub>F(AV)</sub>	180° sinusoidal conduction		12 <sup>(1)</sup>	А
at case temperature	_				150 <sup>(1)</sup>	°C
	Maximum peak one cycle non-repetitive surge current		Half cycle 50 Hz sine wave	Following any rated load condition and with rated V <sub>RRM</sub> applied	230	- A
			or 6 ms rectangular pulse  Half cycle 60 Hz sine wave			
Maximum peak one cy			or 5 ms rectangular pulse		240 <sup>(1)</sup>	
non-repetitive surge c			Half cycle 50 Hz sine wave or 6 ms rectangular pulse	Following any rated load condition and with V <sub>RRM</sub> applied following surge = 0	275	
			Half cycle 60 Hz sine wave or 5 ms rectangular pulse		285	
			t = 10 ms	With rated V <sub>RRM</sub> applied	260	. A <sup>2</sup> s
Maximum I <sup>2</sup> t for fusing	Maximum I <sup>2</sup> t for fusing		t = 8.3 ms	following surge, initial T <sub>J</sub> = 200 °C	240	
Maximum I <sup>2</sup> t for individual		l <sup>2</sup> t	t = 10 ms	With V <sub>RRM</sub> = 0 following surge, initial T <sub>J</sub> = 200 °C	370	
device fusing			t = 8.3 ms		340	
Maximum I <sup>2</sup> √t for individevice fusing	Maximum l <sup>2</sup> √t for individual device fusing		t = 0.1 to 10 ms, V <sub>RRM</sub> = 0 following surge		3715	A²√s
Maximum forward volt	Maximum forward voltage drop		I <sub>F(AV)</sub> = 12 A (38 A peak), T <sub>C</sub> = 25 °C		1.35 <sup>(1)</sup>	V
	V <sub>RRM</sub> = 50				3.0 <sup>(1)</sup>	
	V <sub>RRM</sub> = 100				2.5 (1)	
	V <sub>RRM</sub> = 150				2.25 (1)	
	V <sub>RRM</sub> = 200					mA
	V <sub>RRM</sub> = 300		Maximum rated $I_{F(AV)}$ and $T_{C}$		1.75 <sup>(1)</sup>	
Maximum averagereverse current	V <sub>RRM</sub> = 400	I <sub>R(AV)</sub> (3)			1.5 <sup>(1)</sup>	
	V <sub>RRM</sub> = 500	0			1.25 (1)	
	V <sub>RRM</sub> = 600				1.0 (1)	
	$V_{RRM} = 700$				0.9 (1)	
	V <sub>RRM</sub> = 800					
	V <sub>RRM</sub> = 900				0.7 (1)	
	$V_{RRM} = 1000$				0.6 (1)	

#### Notes

- (1) JEDEC registered values
- (2)  $I^2t$  for time  $t_x = I^2\sqrt{t} \times \sqrt{t_x}$
- $^{(3)}$  Maximum peak reverse current (I\_{RM}) under same conditions  $\approx 2~x$  rated I\_{R(AV)}

Document Number: 93493 Revision: 24-Jun-08





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THERMAL AND MECHAN PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating case and storage temperature range		T <sub>C</sub> , T <sub>Stg</sub>		- 65 to 200 <sup>(1)</sup>	°C
Maximum internal thermal resistance, junction to case		R <sub>thJC</sub>	DC operation	2.0 (1)	°C/W
Thermal resistance, case to sink		R <sub>thCS</sub>	Mounting surface, smooth, flat and greased	0.5	
Mounting torque	minimum		Towns and indicate and the same	1.36 (12)	N ⋅ m (lbf ⋅ in)
	maximum		Torque applied to nut; non-lubricated threads	1.69 (15)	
	minimum		Targetta and the state of the s	1.07 (9.45)	
	maximum		Torque applied to nut; lubricated threads	1.30 (11.55)	
	minimum		Torque applied to device case; lubricated threads	1.17 (10.35)	
	maximum			1.43 (12.65)	
Approximate weight				7.0	g
				0.25	OZ.
Case style JEDEC		JEDEC	DO-203A	A (DO-4)	

Note
(1) JEDEC registered values

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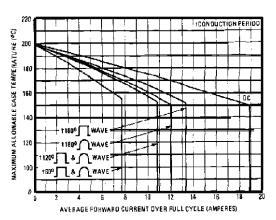


Fig. 1 - Average Forward Current vs. Maximum Allowable Case Temperature

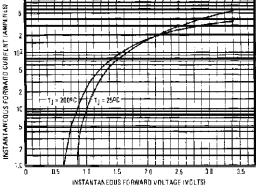


Fig. 4 - Maximum Forward Voltage vs. Forward Current

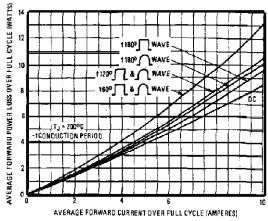


Fig. 2 - Maximum Low Level Forward Power Loss vs. Average Forward Current

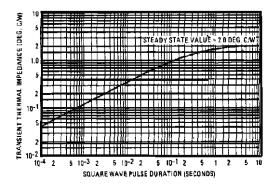


Fig. 5 - Maximum Transient Thermal Impedance, Junction to Case vs. Pulse Duration

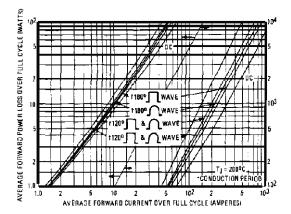


Fig. 3 - Maximum High Level Forward Power Loss vs. Average Forward Current

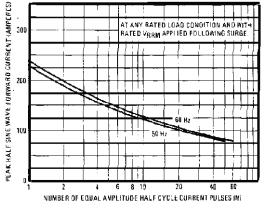


Fig. 6 - Maximum Non-Repetitive 50 Hz Surge Current vs. Number of Current Pulses

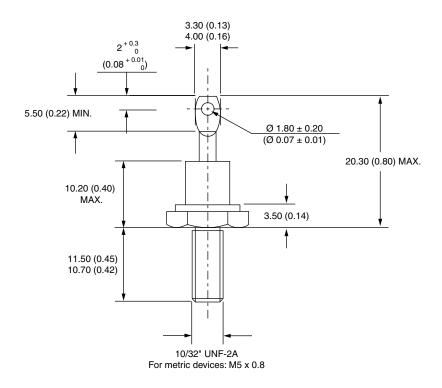
LINKS TO RELATED DOCUMENTS		
Dimensions http://www.vishay.com/doc?95311		

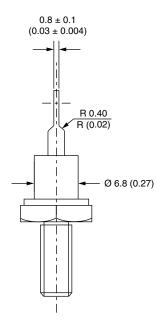


## Vishay Semiconductors

## DO-203AA (DO-4)

#### **DIMENSIONS** in millimeters (inches)







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